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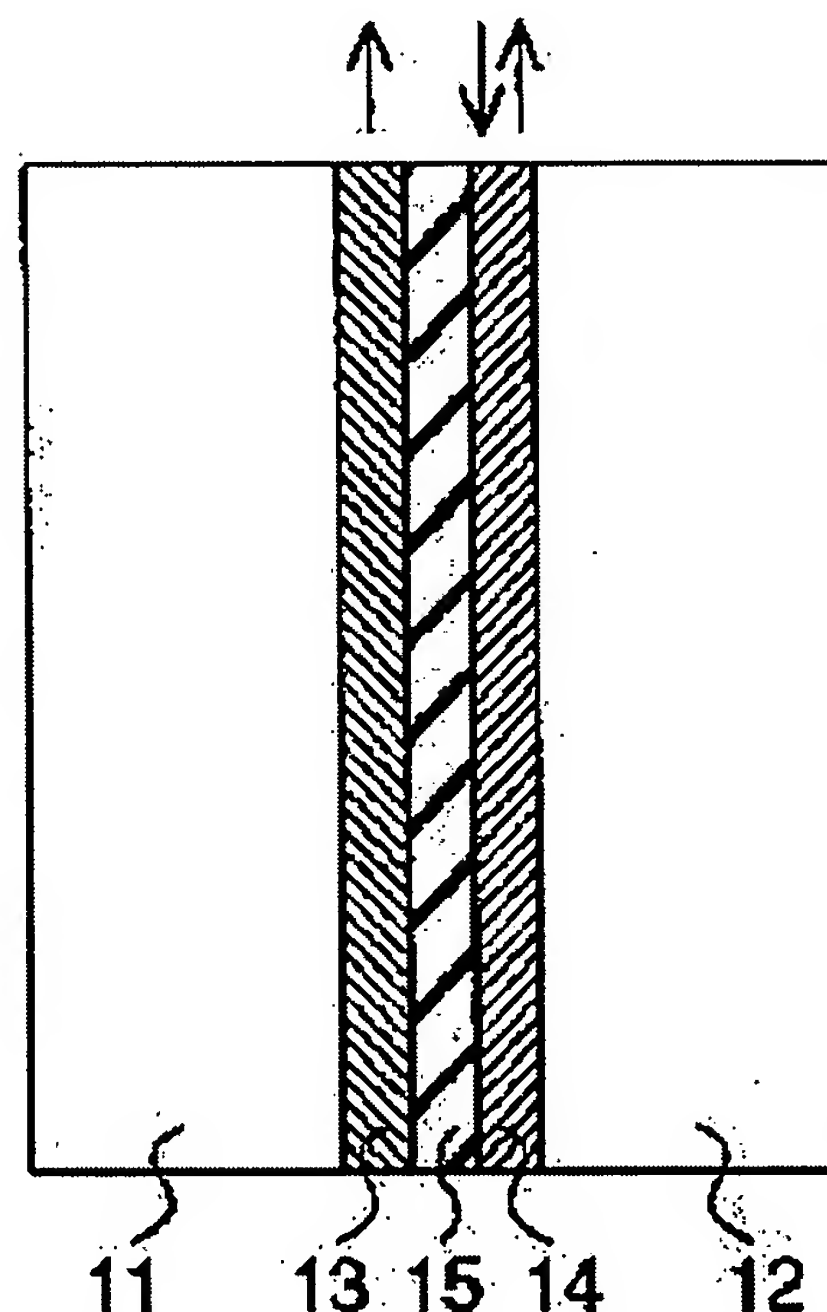
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## (54) MAGNETIC TUNNEL JUNCTION ELEMENT

(57)Abstract:

PROBLEM TO BE SOLVED: To reduce the voltage dependence of a magnetic tunnel junction element and increase the MR ratio of the element.

SOLUTION: A magnetic tunnel junction element is provided with a first magnetic electrode, an insulating layer 15 provided on the electrode, and a second magnetic electrode provided on the insulating layer 15. The second magnetic electrode is constituted in a laminated structure, composed of a first thin film 13 containing iron, cobalt, or nickel and having a thickness of 5 nm or smaller and a second thin film containing a noble metal, copper, or chromium.



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